

**REPLY UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER 2800**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**In Re Application of:** William G. America

**Conf. No.:** 3775

**Serial No.:** 10/709,776

**Art Unit:** 2811

**Filed:** 5/27/2004

**Dkt. #:** FIS920040083US1 (IBMF-0058)

**Title:** SEMICONDUCTOR DEVICE FORMED  
BY IN-SITU MODIFICATION OF  
DIELECTRIC LAYER AND RELATED  
METHODS

**Examiner:** Im, Junghwa M

Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AFTER-FINAL AMENDMENT**

Sir:

**I. INTRODUCTORY COMMENTS**

This paper is being filed in response to the Office Action dated May 17, 2007. Please amend the above-referenced patent application as follows:

*Enter Wrice file on 7-17-07  
J Steptue*